



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D T _A = +25°C | |
|-------------------|--------------------------------|--|--|
| -20V | $36m\Omega$ @ $V_{GS} = -4.5V$ | -5.3A | |
| | $60m\Omega @ V_{GS} = -2.5V$ | -3.9A | |

Description

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

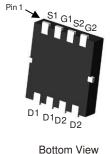
https://www.diodes.com/quality/product-definitions/

Mechanical Data

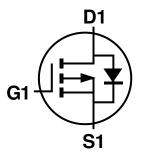
- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.072 grams (Approximate)

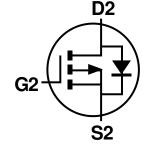
POWERDI3333-8 (Type UXB)





Top View





P-Channel MOSFET

P-Channel MOSFET

Ordering Information (Note 4)

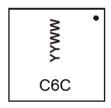
| Part Number | Case | Packaging |
|---------------|--------------------------|------------------|
| DMP2040UND-7 | POWERDI3333-8 (Type UXB) | 2000/Tape & Reel |
| DMP2040UND-13 | POWERDI3333-8 (Type UXB) | 3000/Tape & Reel |

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Document number: DS42189 Rev. 3 - 2



C6C = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 for 2020) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|-----------------|--|----------------|----------------|---|
| Drain-Source Voltage | V_{DSS} | -20 | V | | |
| Gate-Source Voltage | Vgss | ±12 | V | | |
| Continuous Drain Current (Note 6) V _{GS} = -4.5V | Steady State | T _A = +25°C T _A = +70°C | l _D | -5.3 -4.2 | Α |
| Continuous Drain Current (Note 7) $V_{GS} = -4.5V$ Steady $T_C = +25^{\circ}C$ State $T_C = +70^{\circ}C$ | | | lo | -13.6 -10.9 | Α |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | I _{DM} | -25 | Α | | |
| Continuous Source-Drain Diode Current (Note 6) | Is | -1.9 | Α | | |
| Avalanche Current (Note 8) L = 0.1mH | I _{AS} | -19 | Α | | |
| Avalanche Energy (Note 8) L = 0.1mH | Eas | 18 | mJ | | |

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|--|------------------------|------------------|------|------|
| Total Power Dissipation (Note 5) | T _A = +25°C | PD | 0.9 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | R _{0JA} | 148 | °C/W |
| Total Power Dissipation (Note 6) | T _A = +25°C | PD | 1.4 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | $R_{\theta JA}$ | 88 | °C/W |
| Thermal Resistance, Junction to Case (Note 7) | | Rejc | 13.2 | °C/W |
| Operating and Storage Temperature Range | TJ, TSTG | -55 to +150 | °C | |

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|---|---------------------|------|------|------|--------------------------------------|---|--|
| OFF CHARACTERISTICS (Note 9) | | | | | | | |
| Drain-Source Breakdown Voltage | BVDSS | -20 | _ | _ | V | V _G S = 0V, I _D = -250μA | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | -1 | μA $V_{DS} = -16V, V_{GS} = 0V$ | | |
| Gate-Source Leakage | Igss | | _ | ±100 | nA | V _G S = ±12V, V _D S = 0V | |
| ON CHARACTERISTICS (Note 9) | | | | • | | | |
| Gate Threshold Voltage | V _{GS(TH)} | -0.6 | _ | -1.5 | V | $V_{DS} = V_{GS}$, $I_D = -250\mu A$ | |
| Static Drain-Source On-Resistance | D | _ | 28 | 36 | mO. | $V_{GS} = -4.5V, I_{D} = -8.9A$ | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | | 38 | 60 | mΩ | V _{GS} = -2.5V, I _D = -6.9A | |
| Diode Forward Voltage | VsD | _ | -0.7 | -1.2 | V | V _G S = 0V, I _S = -2.9A | |
| DYNAMIC CHARACTERISTICS (Note 10) | | | | | | | |
| Input Capacitance | Ciss | _ | 834 | _ | | V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz | |
| Output Capacitance | Coss | _ | 133 | _ | pF | | |
| Reverse Transfer Capacitance | Crss | _ | 105 | _ | | | |
| Gate Resistance | Rg | _ | 4.9 | _ | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz | |
| Total Gate Charge (V _{GS} = -4.5V) | Qg | _ | 9.6 | _ | | | |
| Total Gate Charge (V _{GS} = -10V) | Qg | _ | 20 | _ | nC | Vps = -6V. lp = -8.9A | |
| Gate-Source Charge | Qgs | _ | 1.1 | _ | IIC | VDS = -6V, ID = -6.9A | |
| Gate-Drain Charge | Q_{gd} | | 2.6 | _ | | | |
| Turn-On Delay Time | t _{D(ON)} | | 14.6 | _ | | | |
| Turn-On Rise Time | tr | | 5.5 | _ | 20 | $V_{DD} = -6V, R_L = 6\Omega$ | |
| Turn-Off Delay Time | tD(OFF) | _ | 38.7 | _ | ns | $V_{GS} = -4.5V$, $R_g = 6\Omega$, $I_D = -1A$ | |
| Turn-Off Fall Time | tF | | 18.3 | _ | | | |
| Body Diode Reverse Recovery Time | t _{RR} | _ | 9.8 | _ | ns | I _F = -8.9A, di/dt = -100A/μs | |
| Body Diode Reverse Recovery Charge | Qrr | _ | 2.7 | _ | nC | IF = -8.9A, di/dt = -100A/μs | |

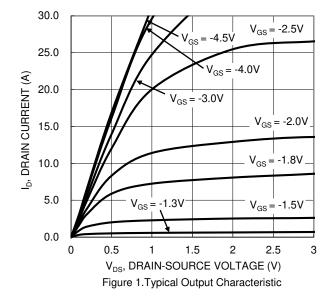
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

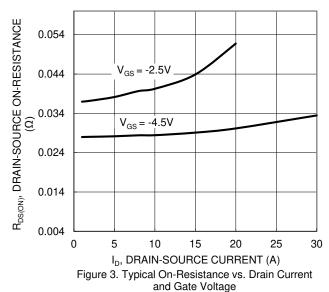
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

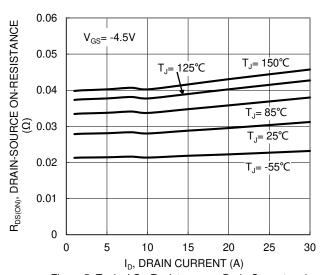
^{7.} Thermal resistance from junction to soldering point (on the exposed drain pad).

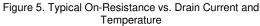
I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

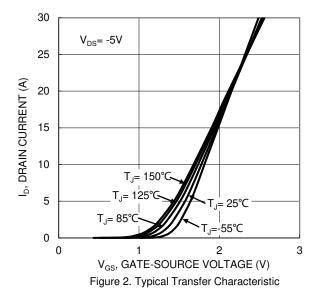


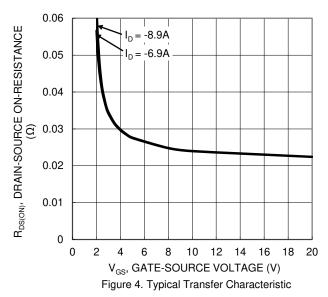












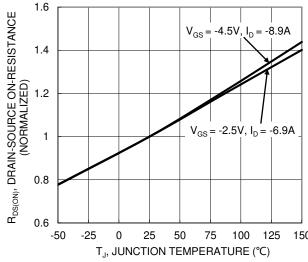


Figure 6. On-Resistance Variation with Temperature



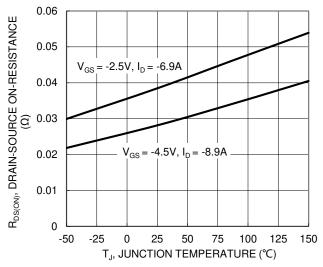
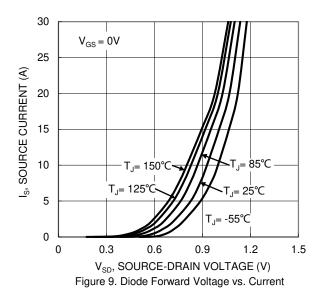


Figure 7. On-Resistance Variation with Temperature



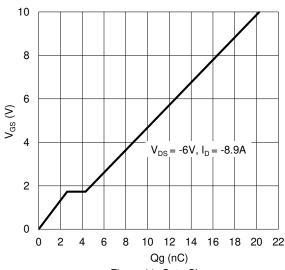


Figure 11. Gate Charge

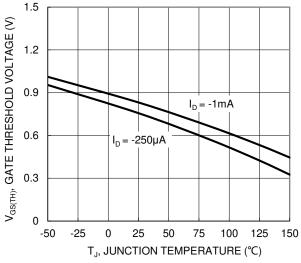
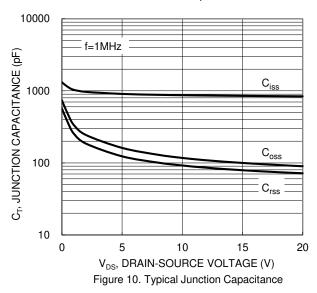


Figure 8. Gate Threshold Variation vs. JunctionTemperature



100 R_{DS(ON)} LIMITED 10 =1ms ≡ ID, DRAIN CURRENT (A) P_w=100µs 1 P_w=100ms $T_{J(MAX)}=150$ °C T_C=25°C Single Pulse DUT on 1*MRP board DC $V_{GS} = -4.5V$ 0.01 10 0.1 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



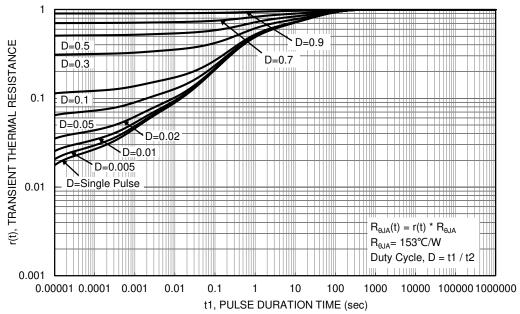


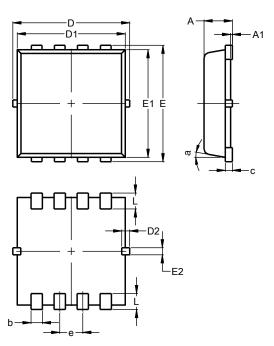
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

POWERDI3333-8 (Type UXB)

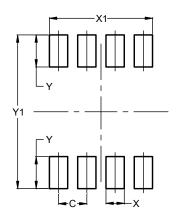


| POWERDI3333-8 (Type UXB) | | | | |
|-----------------------------|------|------|------|--|
| Dim | Min | Max | Тур | |
| Α | 0.75 | 0.85 | 0.80 | |
| A1 | 0.00 | 0.05 | | |
| b | 0.25 | 0.40 | 0.32 | |
| С | 0.10 | 0.25 | 0.15 | |
| D | 3.20 | 3.40 | 3.30 | |
| D1 | 2.95 | 3.15 | 3.05 | |
| D2 | 0.10 | 0.35 | 0.23 | |
| E | 3.20 | 3.40 | 3.30 | |
| E1 | 2.95 | 3.15 | 3.05 | |
| E2 | 0.10 | 0.30 | 0.20 | |
| е | _ | _ | 0.65 | |
| L | 0.35 | 0.55 | 0.45 | |
| а | 0° | 12° | 10° | |
| All Dimensions in mm | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

POWERDI3333-8 (Type UXB)



| Dimensions | Value (in mm) | | |
|------------|---------------|--|--|
| С | 0.650 | | |
| Х | 0.420 | | |
| X1 | 2.370 | | |
| Υ | 0.730 | | |
| Y1 | 3.500 | | |



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